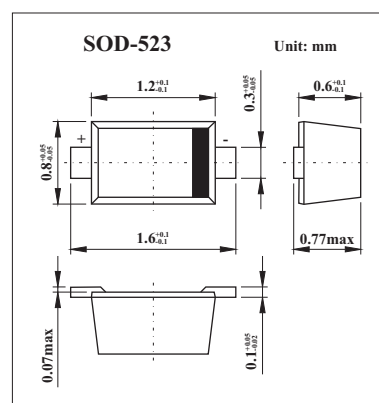


Switching Diode

BAS16X

■ Features

- High-Speed Switching Applications
- Small package.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Units
DC reverse voltage	V_R	75	V
Peak Forward Current	I_F	200	mA
Peak Forward Surge Current	$I_{FM}(\text{surge})$	500	mA
Total Device Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction and storage temperature	T_j, T_{stg}	150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu\text{A}$	75			V
Forward voltage	V_{F1}	$I_F=1\text{mA}$			715	mV
	V_{F2}	$I_F=10\text{mA}$			855	
	V_{F3}	$I_F=50\text{mA}$			1000	
	V_{F4}	$I_F=150\text{mA}$			1250	
Reverse current	I_R	$V_R=75\text{V}$			1.0	μA
Diode capacitance	C_d	$V_R=0\text{V}, f=1\text{MHz}$			2.0	pF
Reverse Recovery Time	t_r	$I_F = I_R = 10\text{mA}, R_L = 50\ \Omega$			6.0	ns